

# UNISONIC TECHNOLOGIES CO., LTD

UT4414 Preliminary Power MOSFET

# N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

#### ■ DESCRIPTION

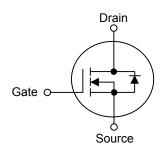
The UTC **UT4414** is an N-channel enhancement mode FET with excellent trench technology to provide customers perfect  $R_{DS(ON)}$  and low gate charge. The source leads are separated to allow a Kelvin connection to the source, which may be used to bypass the source inductance.

This device can be applied in a load switch or in PWM applications.

#### **■** FEATURES

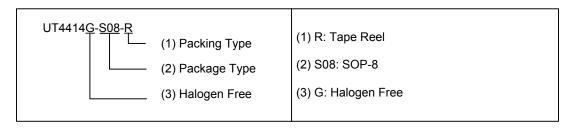
- \*  $V_{DSS} = 30V$
- \* I<sub>D</sub>=8.5A @V<sub>GS</sub>=10V
- \*  $R_{DS(ON)}$ <26m $\Omega$  @ $V_{GS}$ =10V
- \*  $R_{DS(ON)}$ <40m $\Omega$  @ $V_{GS}$ =4.5V

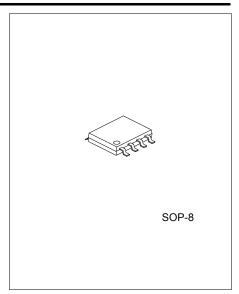
#### ■ SYMBOL



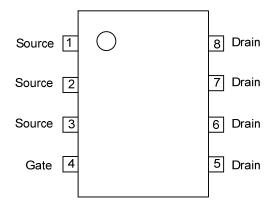
#### ORDERING INFORMATION

Ordering Number	Package	Packing
UT4414G-S08-R	SOP-8	Tape Reel





### ■ PIN CONFIGURATION



# ■ ABSOLUTE MAXIMUM RATING (T<sub>A</sub> =25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain to Source Voltage		$V_{DSS}$	30	V
Gate to Source Voltage		$V_{GSS}$	±20	V
Continuous Drain Current (Note 1)	T <sub>A</sub> =25°C	I <sub>D</sub>	8.5	Α
	T <sub>A</sub> =70°C	$I_D$	7.1	Α
Pulsed Drain Current (Note 1)		I <sub>DM</sub>	50	Α
Total Power Dissipation	T <sub>A</sub> =25°C	В	3	W
	T <sub>A</sub> =70°C	P <sub>D</sub>	2.1	W
Junction Temperature		TJ	+150	°C
Storage Temperature	·	T <sub>STG</sub>	-55 ~ <b>+</b> 150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

#### ■ THERMAL DATA

PARAMETER		SYMBOL	MIN	TYP	MAX	UNIT
Junction to Ambient (Note 1)	t ≤10s	$\theta_{JA}$		31	40	°C/W
	Steady-State			59	75	°C/W

## ■ ELECTRICAL CHARACTERISTICS (T<sub>J</sub> =25°C, unless otherwise specified)

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PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS				÷	-	
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	$V_{GS}$ =0V, $I_D$ =250 $\mu$ A	30			V
Drain-Source Leakage Current	I <sub>DSS</sub>	V <sub>DS</sub> =24V,V <sub>GS</sub> =0V		0.004	1	μΑ
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> =0V ,V <sub>GS</sub> =±20V			100	nA
ON CHARACTERISTICS				÷	-	
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS} = V_{GS}$ , $I_D = 250 \mu A$	1	1.9	3	V
On State Drain Current	I <sub>D(ON)</sub>	V <sub>GS</sub> =4.5V, V <sub>DS</sub> =5V	20			Α
Drain-Source On-State Resistance	В	V <sub>GS</sub> =10V,I <sub>D</sub> =8.5A		20	26	mΩ
	R <sub>DS(ON)</sub>	$V_{GS}$ =4.5V, $I_D$ =5A		31	40	mΩ
Forward Transconductance	<b>g</b> FS	$V_{DS}$ =5 $V$ , $I_{D}$ =5 $A$	10	17		S
DYNAMIC PARAMETERS				÷	-	
Input Capacitance	C <sub>ISS</sub>			680	820	pF
Output Capacitance	Coss	$V_{DS}$ =15V, $V_{GS}$ =0V, $f$ =1MHz		102		pF
Reverse Transfer Capacitance	C <sub>RSS</sub>			77		pF
Gate Resistance	$R_{G}$	$V_{DS}$ =0 $V$ , $V_{GS}$ =0 $V$ , $f$ =1 $MHz$		3	3.6	Ω
SWITCHING PARAMETERS						
Total Gate Charge (10V)	$Q_{G}$			13.84	17	nC
Total Gate Charge (4.5V)	$Q_{G}$	\/ -15\/ \/ -10\/   -9.5A		6.74	8.1	nC
Gate-Source Charge	$Q_{GS}$	$V_{DS}$ =15V, $V_{GS}$ =10V, $I_{D}$ =8.5A		1.84		nC
Gate-Drain Charge	$Q_GD$			3.32		nC
Turn-ON Delay Time	t <sub>D(ON)</sub>			4.5	6.5	ns
Turn-ON Rise Time	t <sub>R</sub>	$V_{DS}$ =15V, $V_{GS}$ =10V, $R_{G}$ =3 $\Omega$ ,		4.2	6.3	ns
Turn-OFF Delay Time	t <sub>D(OFF)</sub>	R <sub>L</sub> =1.8Ω		20.1	30	ns
Turn-OFF Fall Time	t <sub>F</sub>			4.9	7.5	ns
SOURCE- DRAIN DIODE RATINGS AND C	HARACTERI	STICS				
Maximum Body-Diode Continuous Current	Is				4.3	Α
Drain-Source Diode Forward Voltage	$V_{SD}$	I <sub>S</sub> =1A, V <sub>GS</sub> =0V		0.76	1	V
Body Diode Reverse Recovery Time	t <sub>RR</sub>	I <sub>F</sub> =8.5A, dI/dt=100A/μs		17.2	21	ns
Body Diode Reverse Recovery Charge	$Q_{RR}$	I <sub>F</sub> =8.5A, dI/dt=100A/μs		8.6	10	nC
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- Note: 1. The value of  $\theta_{JA}$  is measured with the device mounted on  $1\text{in}^2$  FR-4 board with 2oz. Copper, in a still air environment with  $T_A$ =25°C. The value in any given application depends on the user's specific boar design. The current rating is based on the t ≤ 10s thermal resistance rating.
  - 2. Repetitive Rating : Pulse width limited by  $T_{\mathsf{J}}$
  - 3. The  $\theta_{JA}$  is the sum of the thermal impedance from junction to lead  $\theta_{JL}$  and lead to ambient.



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